

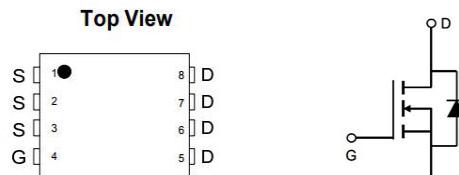
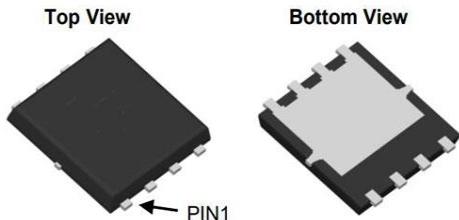
30V /60A Single N Power MOSFET
General Description

30V /60A Single N Power MOSFET

Very low on-resistance RDS(on) @ VGS=4.5 V

Pb-free lead plating; RoHS compliant

| | | |
|---------------------------------------|-----|----|
| V_{DS} | 30 | V |
| R_{DS(on),TYP@VGS=10V} | 6.0 | mΩ |
| R_{DS(on),TYP@VGS=4.5} | 9.5 | mΩ |
| I_D | 60 | A |



| Part ID | Package Type | Marking | Tape and reel infomation |
|------------|--------------|---------|--------------------------|
| SM6362D1RL | DFN5x6 | 6362 | 3000 |


 100% UIS Tested
100% RG Tested

| Parameter | Symbol | Maximum | Units |
|--|-----------------------------------|------------|-------|
| Drain-Source Voltage | V _{DS} | 30 | V |
| Gate-Source Voltage | V _{GS} | 20 | ±V |
| Continuous Drain Current A | I _D | 60.0 | A |
| | | 39* | |
| Pulsed Drain Current B | I _{DM} | 96.0 | |
| Avalanche Current G | I _{AR} | 19.2 | |
| Repetitive avalanche energy L=0.1mH G | E _{AR} | 44.2 | mJ |
| Power Dissipation A | P _D | 31 | W |
| | | 13* | |
| Junction and Storage Temperature Range | T _J , T _{STG} | -55 to 150 | °C |

Thermal Characteristics

| Parameter | Symbol | Typ | Max | Units |
|-------------------------------|------------------|-----|-----|-------|
| Maximum Junction-to-Ambient A | R _{θJA} | 21 | 32 | °C/W |
| Maximum Junction-to-Ambient A | | 43 | 51 | °C/W |
| Maximum Junction-to-Lead c | R _{θJL} | 12 | 20 | °C/W |

STATIC PARAMETERS

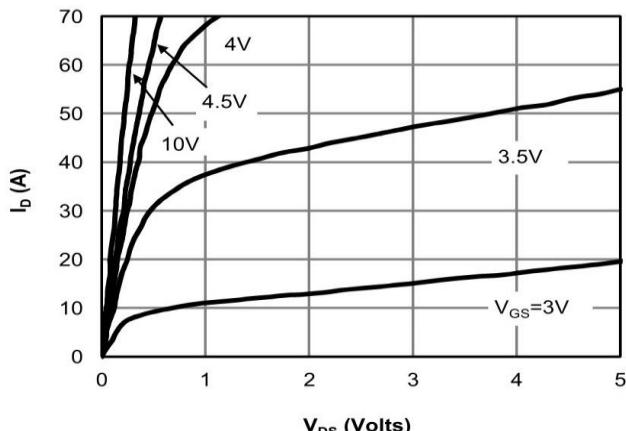
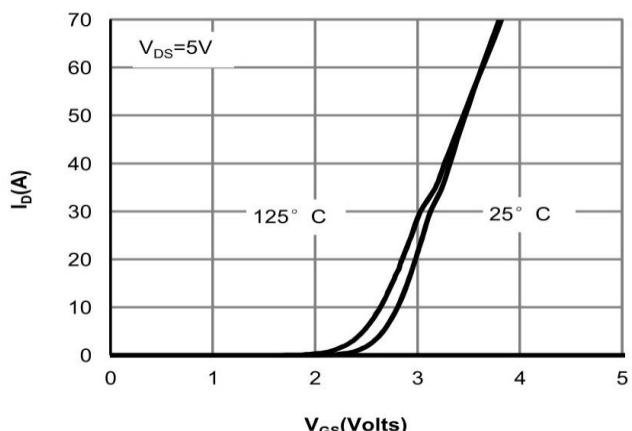
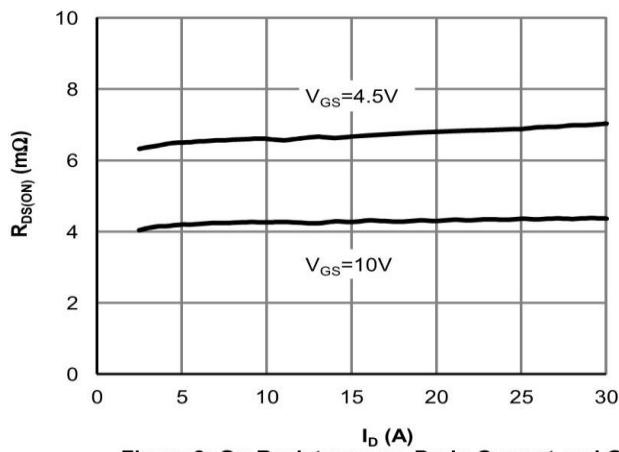
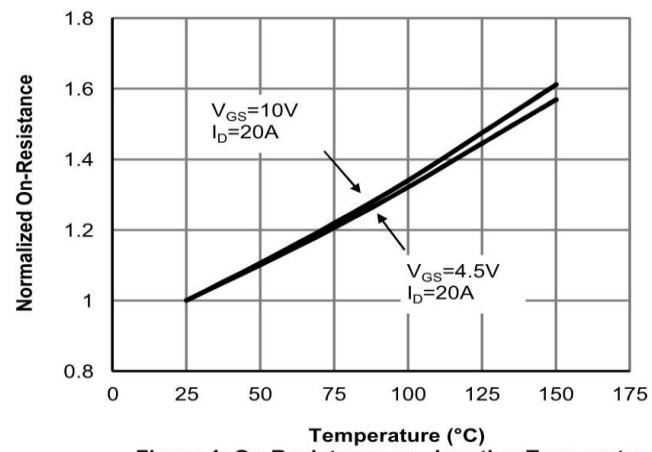
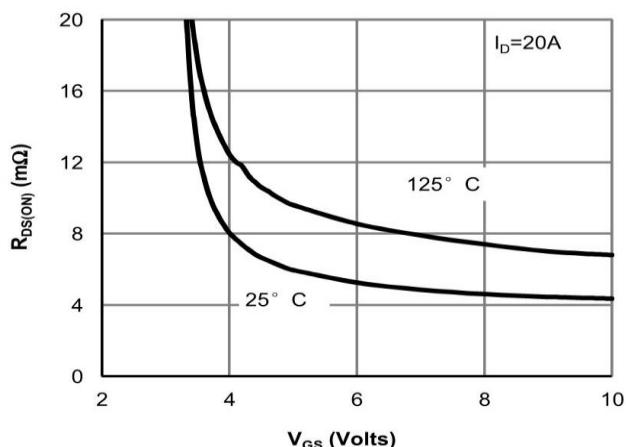
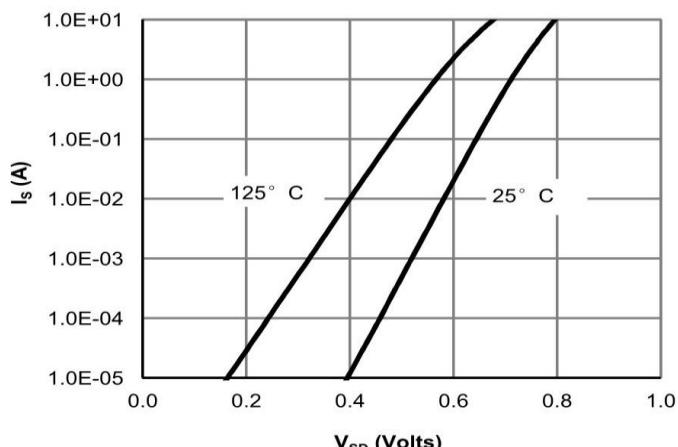
| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|--------------|---------------------------------------|-----------------------------------|-----|------|-----------|-----------|
| BV_{DSS} | Drain-Source Breakdown Voltage | $I_D = -250\mu A, V_{GS} = 0V$ | 30 | | | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS}=30V, V_{GS}=0V$ | | | 1 | uA |
| | | | | | 5 | |
| I_{GSS} | Gate-Body leakage current | $V_{DS} = 0V, V_{GS} = \pm 20V$ | | | ± 100 | nA |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250\mu A$ | 1.1 | 1.7 | 2.2 | V |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance | $V_{GS}=10V, I_D=20A$ | | 6.0 | 8.6 | $m\Omega$ |
| | | $V_{GS}=4.5V, I_D=20A$ | | 9.5 | 12.3 | |
| g_{FS} | Forward Transconductance | $V_{DS}=5V, I_D=20A$ | | 75 | | S |
| V_{SD} | Diode Forward Voltage | $I_S=1A, V_{GS}=190V$ | | 0.72 | 1 | V |
| I_S | Maximum Body-Diode Continuous Current | | | | 60 | A |

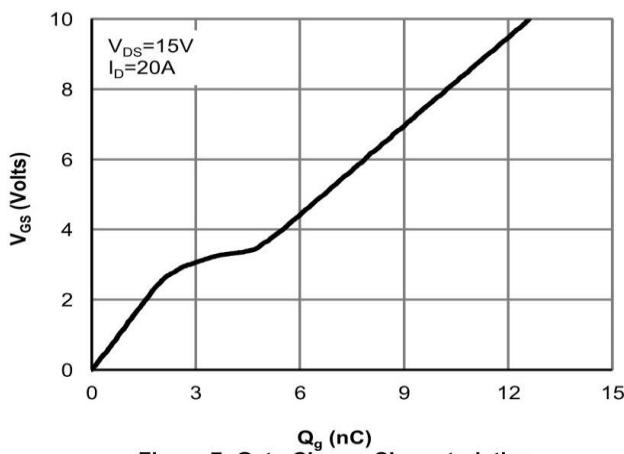
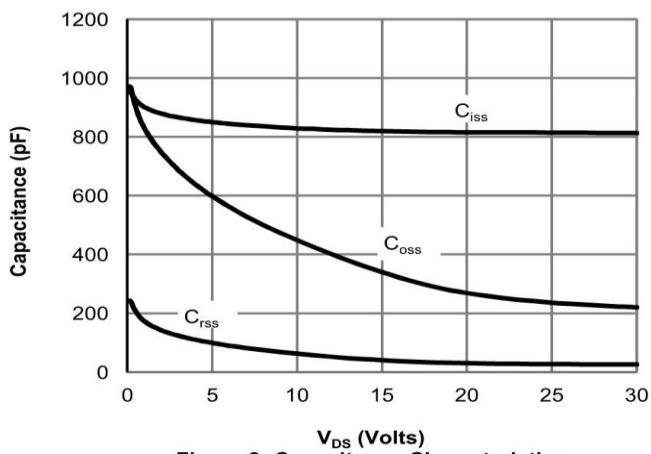
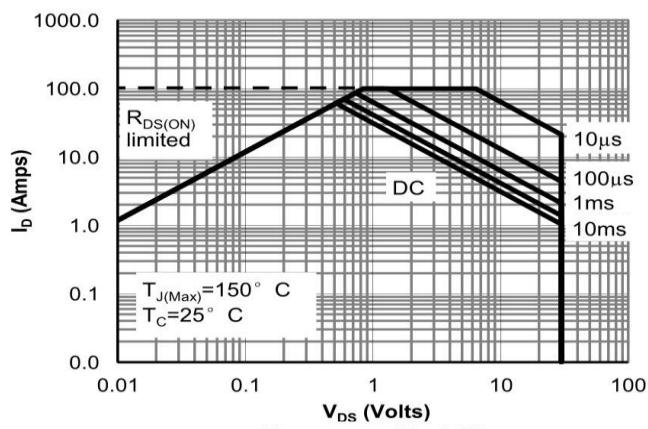
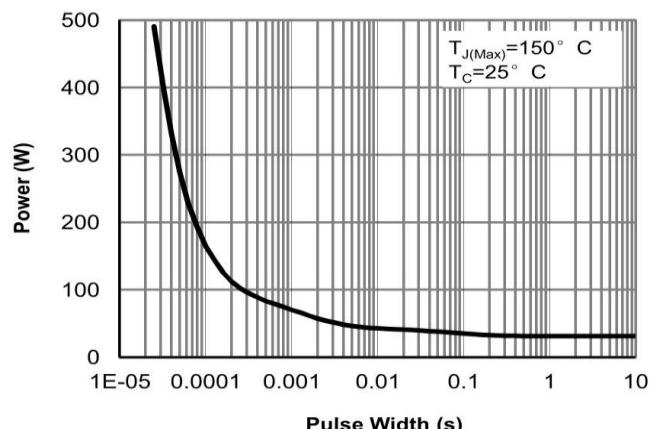
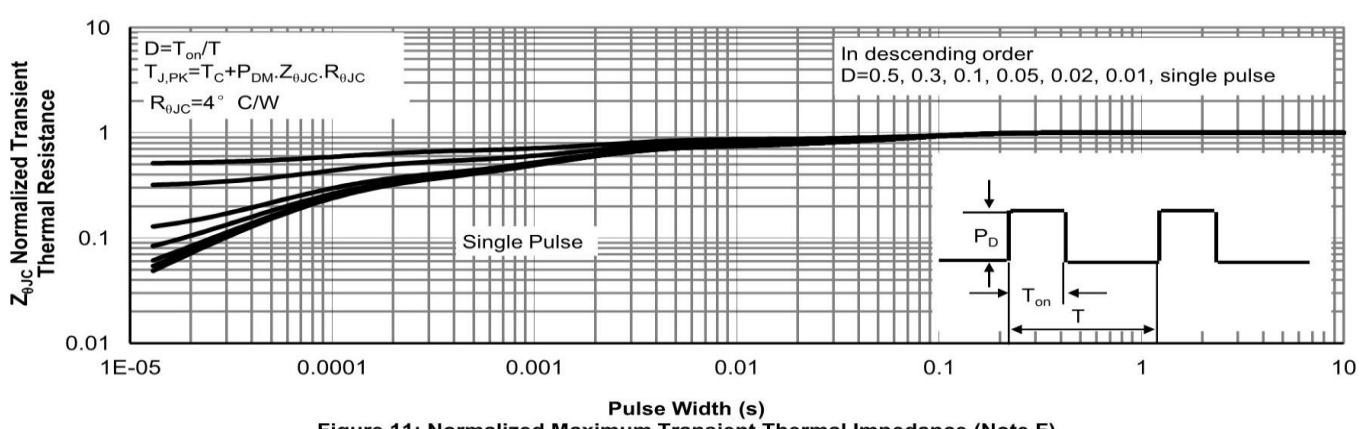
DYNAMIC PARAMETERS

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|-----------|------------------------------|---------------------------------|-----|-----|------|----------|
| C_{iss} | Input Capacitance | $V_{GS}=0V, V_{DS}=15V, f=1MHz$ | | 820 | 1000 | pF |
| C_{oss} | Output Capacitance | | | 340 | 418 | pF |
| C_{rss} | Reverse Transfer Capacitance | | | 40 | 47 | pF |
| R_g | Gate resistance | $V_{GS}=0V, V_{DS}=0V, f=1MHz$ | | | 1.2 | Ω |

SWITCHING PARAMETERS

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|--------------|------------------------------------|--|-----|------|-----|-------|
| $Q_g(10V)$ | Total Gate Charge | $V_{GS}=10V, V_{DS}=15V, I_D=20A$ | | 6.1 | | nC |
| $Q_g 4.5V$ | Total Gate Charge | | | 3.05 | | |
| Q_{gs} | Gate Source Charge | | | 1.68 | | |
| Q_{gd} | Gate Drain Charge | | | 2.4 | | |
| $t_{D(on)}$ | Turn-On Delay Time | $V_{GS}=10V, V_{DS}=15V, RL=0.75\Omega, R_{GEN}=3\Omega$ | | 5.5 | | ns |
| t_r | Turn-On Rise Time | | | 4.4 | | |
| $t_{D(off)}$ | Turn-Off Delay Time | | | 15.4 | | |
| t_f | Turn-Off Fall Time | | | 4.95 | | |
| t_{rr} | Body Diode Reverse Recovery Time | $I_F=-8A, dI/dt=500A/\mu s$ | | 11 | | ns |
| Q_{rr} | Body Diode Reverse Recovery Charge | $I_F=18A, dI/dt=500A/\mu s$ | | 19 | | nC |

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 1: On-Region Characteristics (Note E)

Figure 2: Transfer Characteristics (Note E)

Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

Figure 4: On-Resistance vs. Junction Temperature (Note E)

Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 7: Gate-Charge Characteristics

Figure 8: Capacitance Characteristics

Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

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